4V Drive Nch MOSFET

RSQ045N03

●Structure

Silicon N-channel MOSFET

● Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT6).
- 3) Low voltage drive (4V drive).

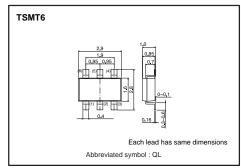
Applications

Switching

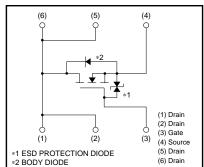
Packaging specifications

	Package	Taping
Type	Code	TR
	Basic ordering unit (pieces)	3000
RSQ045N03		0

● Dimensions (Unit: mm)



●Inner circuit



● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V _{DSS}	30	V	
Gate-source voltage		Vgss	20	V	
Drain current	Continuous	I _D	±4.5	Α	
Drain current	Pulsed	I _{DP} *1	±18	Α	
Source current	Continuous	Is	1.0	Α	
(Body diode)	Pulsed	I _{SP} *1	18	Α	
Total power dissipation		Pp *2	1.25	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

^{*1} Pw≤10μs, Duty cycle≤1%

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	100	°C/W

Rev.A

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	10	μΑ	V _{GS} =20V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	30	-	-	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	_	1	μΑ	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.5	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance		_	27	38	mΩ	I _D = 4.5A, V _G S= 10V
	RDS (on)*	_	36	51	mΩ	ID= 4.5A, VGS= 4.5V
		-	40	56	mΩ	I _D = 4.5A, V _{GS} = 4V
Forward transfer admittance	Y _{fs} *	3.5	-	-	S	V _{DS} = 10V, I _D = 4.5A
Input capacitance	Ciss	_	520	_	pF	V _{DS} = 10V
Output capacitance	Coss	-	150	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	-	95	-	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	12	-	ns	Vpp≒ 15V
Rise time	tr *	-	19	_	ns	ID= 2.25A
Turn-off delay time	t _{d (off)} *	-	41	_	ns	Vgs= 10V RL=6.67Ω
Fall time	t _f *	-	14	_	ns	R _G =10Ω
Total gate charge	Qg *	_	6.8	9.5	nC	V _{DD} ≒15V V _{GS} =5V
Gate-source charge	Q _{gs} *	-	1.6	-	nC	I _D = 4.5A
Gate-drain charge	Q _{gd} *	_	2.3	_	nC	R _L =3.33Ω R _G =10Ω

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	-	_	1.2	V	I _S = 1.0A, V _{GS} =0V

•Electrical characteristic curves

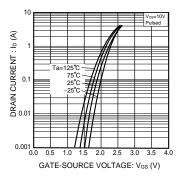


Fig.1 Typical Transfer Characteristics

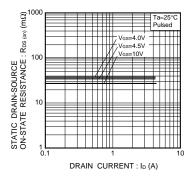


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (I)

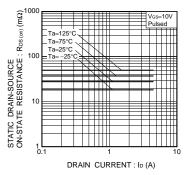
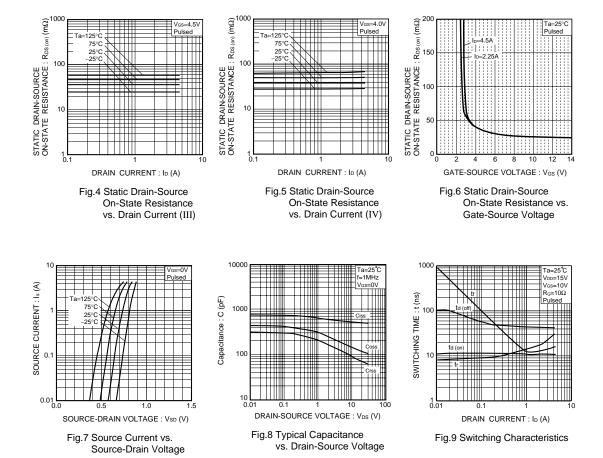


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (II)



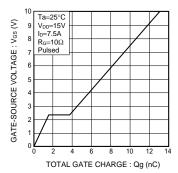


Fig.10 Dynamic Input Characteristics

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